Zener Diode

### DZ6J068S0R

# **Panasonic**

## DZ6J068S0R

## Silicon epitaxial planar type

For surge absorption circuit

#### ■ Features

- · Excellent rising characteristics of zener current Iz
- · Low zener operating resistance Rz
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: 12
- Basic Part Number : Dual DZ3X068D (Individual)

#### Packaging

Embossed type (Thermo-compression sealing) 3 000 pcs / reel (standard)

#### ■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Total power dissipation *1	PT	150	mW
Electrostatic discharge *2	ESD	±10	kV
Junction temperature	Tj	150	°C
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +150	°C

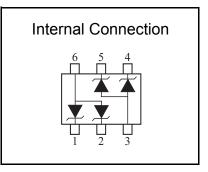
Note) \*1: Mounted on glass epoxy print board. ( 45 mm x 45 mm x 1 mm) (4 Diode total)

Solder in (0.4 mm x 0.8 mm)

\*2: Test method:IEC61000\_4\_2(C = 150 pF,R = 330  $\Omega$ , Contact discharge:10 times)

## Unit: mm 0.2 0.7 (0. 65)(0. 65) 1.3 4. Cathode3 1. Cathode1 2. Cathode2 5. Cathode4 3. Anode3,4 6. Anode1,2

Panasonic	SMini6-F3-B		
JEITA	SC-113DB		
Code	SOT-363		



#### ■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Forward voltage	VF	IF = 10 mA			1.0	V
Zener voltage *1, *2	VZ	IZ = 5 mA	6.46		7.14	V
Zener operating resistance	RZ	IZ = 5 mA			30	Ω
Zener rise operating resistance	RZK	IZ = 0.5 mA			60	Ω
Reverse current	IR	VR = 4 V			0.1	μA
Temperature coefficient of zener voltage *3	SZ	IZ = 5 mA		3.1		mV/°C

- Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.
  - 2. \*1: The temperature must be controlled 25°C for VZ mesurement. VZ value measured at other temperature must be adjusted to VZ (25°C)
    - \*2: VZ guaranted 20 ms after current flow.
    - \*3: Tj = 25°C to 150°C

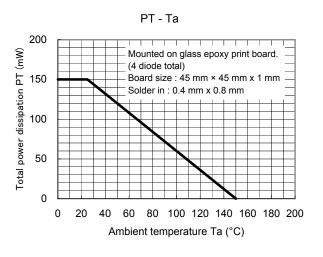
Established: 2010-04-22 Revised : 2013-11-01 Revision. 3

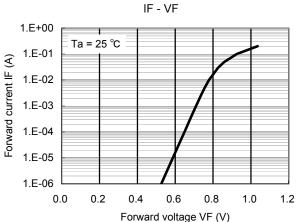
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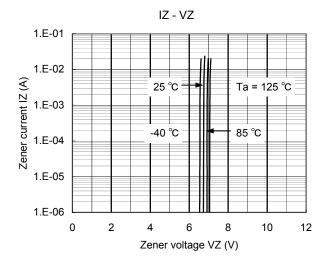
Zener Diode

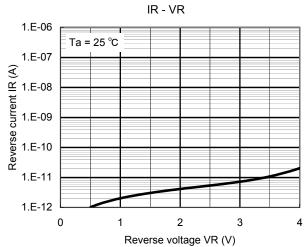
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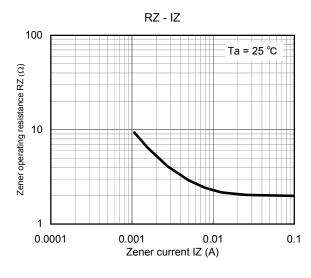
## Technical Data (reference)

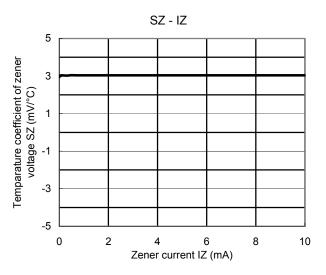












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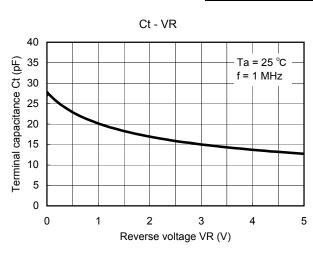
Doc No. TT4-EA-12555 Revision. 3

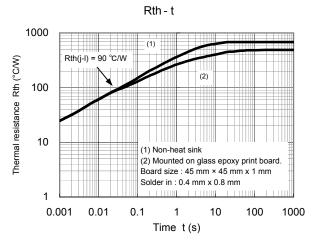
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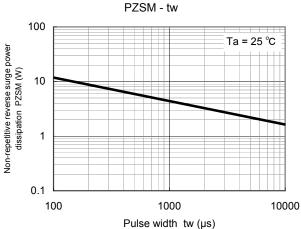
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## Technical Data (reference)







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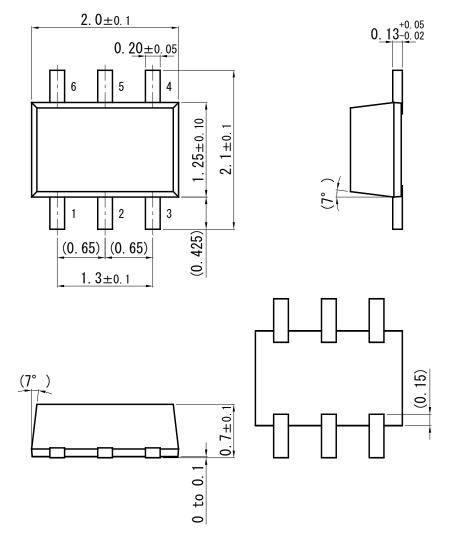
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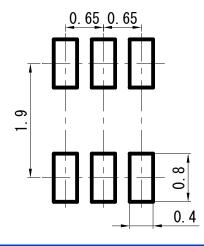
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SMini6-F3-B

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



Established: 2010-04-22 Revised: 2013-11-01

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